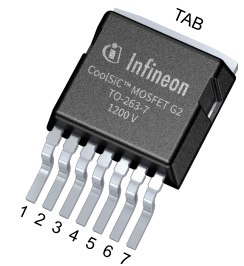


### Final datasheet

### CoolSiC™ 1200 V SiC MOSFET G2 : Silicon Carbide MOSFET

#### Features

- $V_{DS} = 1200\text{ V}$  at  $T_{vj} = 25^\circ\text{C}$
- $I_{DC} = 21\text{ A}$  at  $T_C = 100^\circ\text{C}$
- $R_{DS(on)} = 78.1\text{ m}\Omega$  at  $V_{GS} = 18\text{ V}$ ,  $T_{vj} = 25^\circ\text{C}$
- Very low switching losses
- Overload operation up to  $T_{vj} = 200^\circ\text{C}$
- Short circuit withstand time  $2\ \mu\text{s}$
- Benchmark gate threshold voltage,  $V_{GS(th)} = 4.2\text{ V}$
- Robust against parasitic turn on, 0 V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>



- Halogen-free
- Green
- Lead-free
- RoHS

#### Potential applications

- EV-Charging
- Online UPS/Industrial UPS
- Solar power optimizer
- String inverter
- General purpose drives (GPD)

#### Product validation

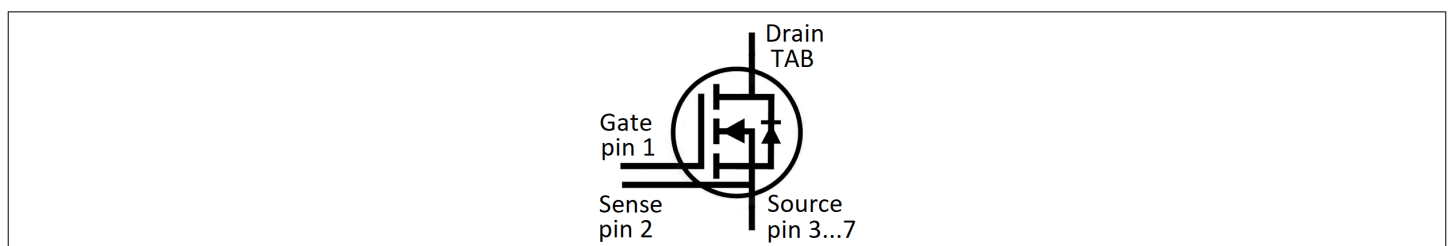
- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

#### Description

Pin definition:

- Pin 1 - Gate
- Pin 2 - Kelvin sense contact
- Pin 3...7 - Source
- Tab - Drain

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction (only for 4pin, TO263-7L)



Type	Package	Marking
IMBG120R078M2H	PG-TO263-7-HV-ND5.8	12M2H078

## Table of contents

	<b>Description</b> .....	1
	<b>Features</b> .....	1
	<b>Potential applications</b> .....	1
	<b>Product validation</b> .....	1
	<b>Table of contents</b> .....	2
<b>1</b>	<b>Package</b> .....	3
<b>2</b>	<b>MOSFET</b> .....	3
<b>3</b>	<b>Body diode (MOSFET)</b> .....	6
<b>4</b>	<b>Characteristics diagrams</b> .....	8
<b>5</b>	<b>Package outlines</b> .....	14
<b>6</b>	<b>Testing conditions</b> .....	15
	<b>Revision history</b> .....	16
	<b>Disclaimer</b> .....	17

## 1 Package

**Table 1** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	$T_{stg}$		-55		150	°C
Soldering temperature	$T_{sold}$	reflow soldering (MSL1 according to JEDEC J-STA-020)			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				62	K/W
MOSFET/body diode thermal resistance, junction-case	$R_{th(j-c)}$			0.73	0.95	K/W

## 2 MOSFET

**Table 2** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage	$V_{DSS}$	$T_{vj} \geq 25 \text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$ , limited by $T_{vj(max)}$	$I_{DDC}$	$V_{GS} = 18 \text{ V}$	$T_c = 25 \text{ °C}$	29	A
			$T_c = 100 \text{ °C}$	21	
Peak drain current, $t_p$ limited by $T_{vj(max)}$ <sup>1)</sup>	$I_{DM}$	$V_{GS} = 18 \text{ V}$	63	A	
Gate-source voltage, max. transient voltage	$V_{GS}$	$t_p \leq 0.5 \text{ }\mu\text{s}$ , $D < 0.01$	-10...23	V	
Gate-source voltage, max. static voltage	$V_{GS}$		-7...20	V	
Avalanche energy, single pulse	$E_{AS}$	$I_D = 8.9 \text{ A}$ , $V_{DD} = 50 \text{ V}$ , $L = 2.8 \text{ mH}$	112	mJ	
Avalanche energy, repetitive	$E_{AR}$	$I_D = 8.9 \text{ A}$ , $V_{DD} = 50 \text{ V}$ , $L = 14.1 \text{ mH}$	0.56	mJ	
Short-circuit withstand time	$t_{SC}$	$V_{DD} \leq 800 \text{ V}$ , $V_{DS,peak} < 1200 \text{ V}$ , $V_{GS(on)} = 15 \text{ V}$ , $T_{vj(start)} = 25 \text{ °C}$	2	$\mu\text{s}$	
Power dissipation, limited by $T_{vj(max)}$	$P_{tot}$		$T_c = 25 \text{ °C}$	158	W
			$T_c = 100 \text{ °C}$	79	

1) verified by design.

**Table 3 Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		15...18	V
Recommended turn-off gate voltage	$V_{GS(off)}$		-5...0	V

**Table 4 Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 8.9\text{ A}$	$T_{vj} = 25\text{ °C}$ , $V_{GS(on)} = 18\text{ V}$	78.1		mΩ
			$T_{vj} = 150\text{ °C}$ , $V_{GS(on)} = 18\text{ V}$	159	206	
			$T_{vj} = 175\text{ °C}$ , $V_{GS(on)} = 18\text{ V}$	185		
			$T_{vj} = 25\text{ °C}$ , $V_{GS(on)} = 15\text{ V}$	97.5		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 2.8\text{ mA}$ , $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$ )	$T_{vj} = 25\text{ °C}$	3.5	4.2	V
			$T_{vj} = 175\text{ °C}$		3.2	
Zero gate-voltage drain current	$I_{DSS}$	$V_{DS} = 1200\text{ V}$ , $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		80	μA
			$T_{vj} = 175\text{ °C}$		1.3	
Gate leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}$	$V_{GS} = 23\text{ V}$		120	nA
			$V_{GS} = -10\text{ V}$		-120	
Forward transconductance	$g_{fs}$	$I_D = 8.9\text{ A}$ , $V_{DS} = 20\text{ V}$		4.1		S
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$ , $V_{AC} = 25\text{ mV}$		10		Ω
Input capacitance	$C_{iss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$		700		pF
Output capacitance	$C_{oss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$		28		pF
Reverse transfer capacitance	$C_{rss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$		2.4		pF
$C_{oss}$ stored energy	$E_{oss}$	$V_{DD} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $V_{AC} = 25\text{ mV}$		12		μJ
Output charge	$Q_{oss}$	Calculated by $C_{oss}(f)V_{DS}$ @100 kHz		43.4		nC
Effective output capacitance, energy related	$C_{o(er)}$	$V_{DD} = 0...800\text{ V}$ , $V_{GS} = 0\text{ V}$		37.5		pF
Effective output capacitance, time related	$C_{o(tr)}$	$I_C = \text{constant}$ , $V_{DD} = 0...800\text{ V}$ , $V_{GS} = 0\text{ V}$		54.2		pF
Total gate charge	$Q_G$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = -2/18\text{ V}$ , turn-on pulse		20.6		nC

**(table continues...)**

**Table 4 (continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = -2/18\text{ V}$ , turn-on pulse		4.6		nC
Gate-to-drain charge	$Q_{GD}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = -2/18\text{ V}$ , turn-on pulse		5.3		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	1.7		
Rise time	$t_r$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	13.4		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	13.3		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.4		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	6		
Fall time	$t_f$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	2.4		
Turn-on energy	$E_{on}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	49		$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$	95		
Turn-off energy	$E_{off}$	$V_{DD} = 800\text{ V}$ , $I_D = 8.9\text{ A}$ , $V_{GS} = 0/18\text{ V}$ , $R_{GS(on)} = 2.3\ \Omega$ , $R_{GS(off)} = 2.3\ \Omega$ , $L_\sigma = 15\text{ nH}$ , diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	16		$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$	19.7		

(table continues...)

3 Body diode (MOSFET)

**Table 4** (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Total switching energy <sup>1)</sup>	$E_{tot}$	$V_{DD} = 800\text{ V}, I_D = 8.9\text{ A},$ $V_{GS} = 0/18\text{ V},$ $R_{GS(on)} = 2.3\ \Omega,$ $R_{GS(off)} = 2.3\ \Omega,$ $L_\sigma = 15\text{ nH},$ diode: body diode at $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		96	$\mu\text{J}$
			$T_{vj} = 175\text{ }^\circ\text{C}$		201.7	
Virtual junction temperature	$T_{vj}$		-55		175	$^\circ\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h <sup>2)</sup>			200	$^\circ\text{C}$

1) including  $E_{fr}$

2) up to 5000 cycles. Maximum  $\Delta T$  limited to 100 K.

**Note:** The chip technology was characterized up to 200 kV/ $\mu\text{s}$ . The measured  $dV/dt$  was limited by measurement test setup and package.

Characteristics at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified.

### 3 Body diode (MOSFET)

**Table 5** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	$V_{DSS}$	$T_{vj} \geq 25\text{ }^\circ\text{C}$	1200	V
Peak reverse drain current, $t_p$ limited by $T_{vj(max)}$	$I_{SM}$	$V_{GS} = 0\text{ V}$	23	A

**Table 6** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Drain-source reverse voltage	$V_{SD}$	$I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		4.2	V
			$T_{vj} = 100\text{ }^\circ\text{C}$		4.11	
			$T_{vj} = 175\text{ }^\circ\text{C}$		4.05	
MOSFET forward recovery charge	$Q_{fr}$	$V_{DD} = 800\text{ V},$ $I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V},$ $di_{SD}/dt = 1000\text{ A}/\mu\text{s},$ $Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ }^\circ\text{C}$		0.13	$\mu\text{C}$
			$T_{vj} = 175\text{ }^\circ\text{C}$		0.21	
MOSFET peak forward recovery current	$I_{frm}$	$V_{DD} = 800\text{ V},$ $I_{SD} = 8.9\text{ A}, V_{GS} = 0\text{ V},$ $di_{SD}/dt = 1000\text{ A}/\mu\text{s},$ $Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ }^\circ\text{C}$		4.5	A
			$T_{vj} = 175\text{ }^\circ\text{C}$		6.1	

(table continues...)

**Table 6** (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
MOSFET forward recovery energy	$E_{fr}$	$V_{DD} = 800\text{ V}$ , $I_{SD} = 8.9\text{ A}$ , $V_{GS} = 0\text{ V}$ , $di_{SD}/dt = 1000\text{ A}/\mu\text{s}$ , $Q_{fr}$ includes also $Q_C$	$T_{vj} = 25\text{ °C}$		31	$\mu\text{J}$
			$T_{vj} = 175\text{ °C}$		87	
Virtual junction temperature	$T_{vj}$		-55		175	$^{\circ}\text{C}$
Virtual junction temperature	$T_{vj(over)}$	overload, cumulative max. 100 h <sup>1)</sup>			200	$^{\circ}\text{C}$

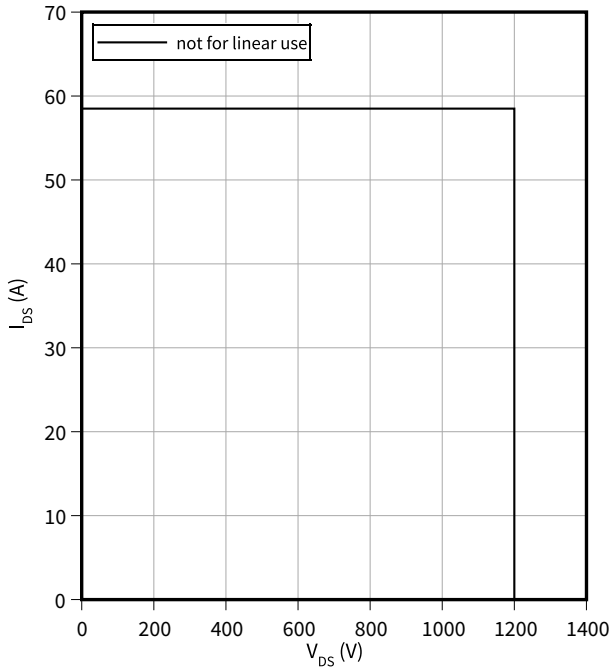
1) up to 5000 cycles. Maximum  $\Delta T$  limited to 100 K.

## 4 Characteristics diagrams

### Reverse bias safe operating area (RBSOA)

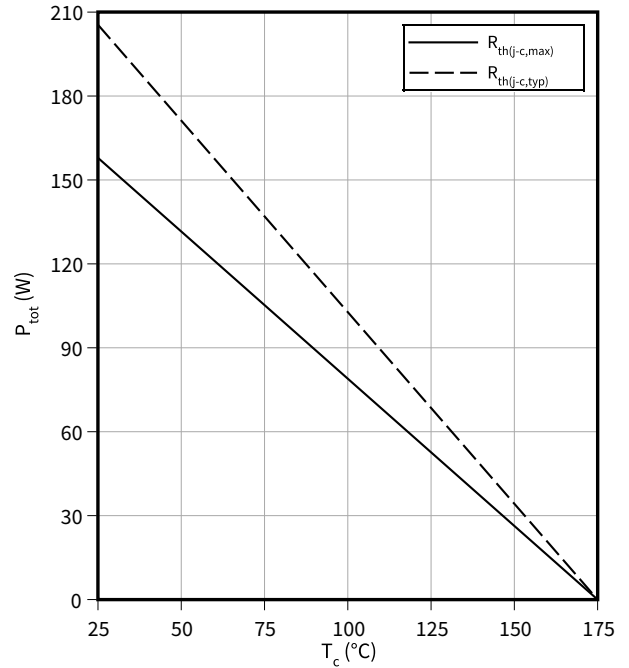
$$I_{DS} = f(V_{DS})$$

$$T_{vj} \leq 200 \text{ }^\circ\text{C}, V_{GS} = 0/18 \text{ V}, T_c = 25 \text{ }^\circ\text{C}$$



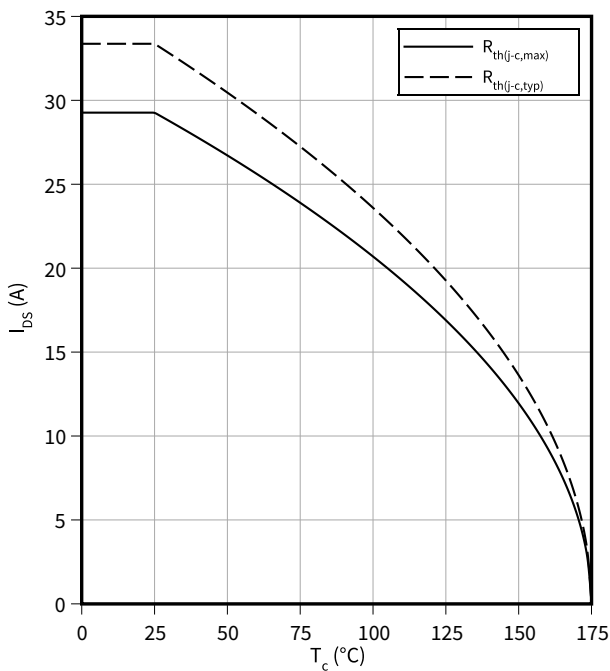
### Power dissipation as a function of case temperature

$$P_{tot} = f(T_c)$$



### Maximum DC drain to source current as a function of case temperature limited by bond wire

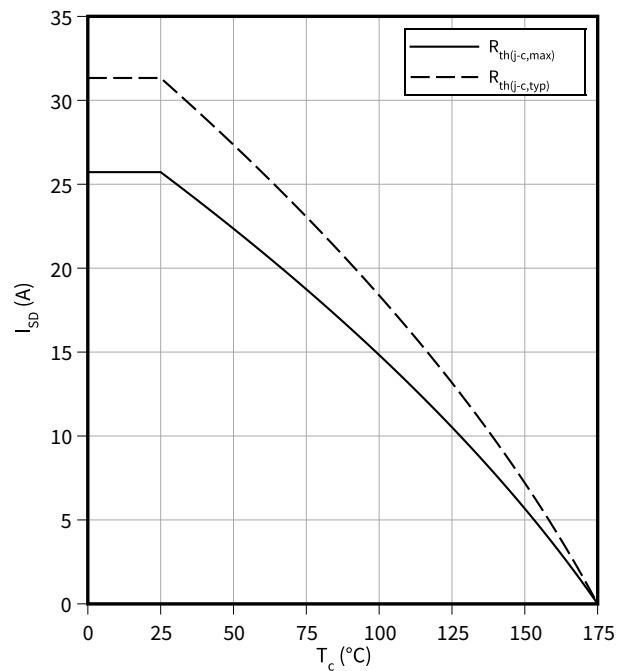
$$I_{DS} = f(T_c)$$



### Maximum source to drain current as a function of case temperature limited by bond wire

$$I_{SD} = f(T_c)$$

$$V_{GS} = 0 \text{ V}$$

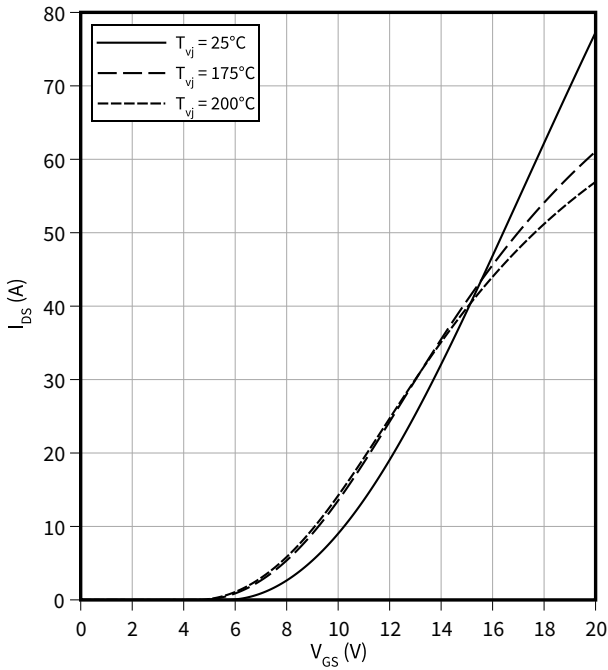




4 Characteristics diagrams

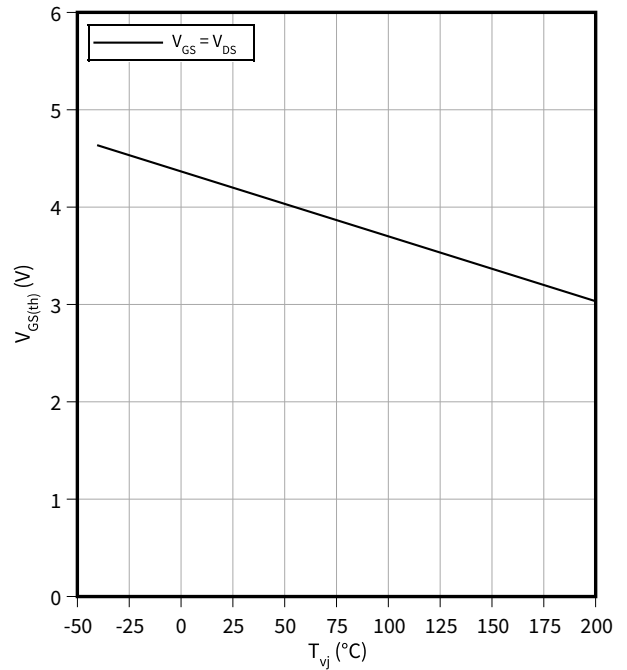
**Typical transfer characteristic**

$I_{DS} = f(V_{GS})$   
 $V_{DS} = 20\text{ V}$ ,  $t_p = 20\ \mu\text{s}$



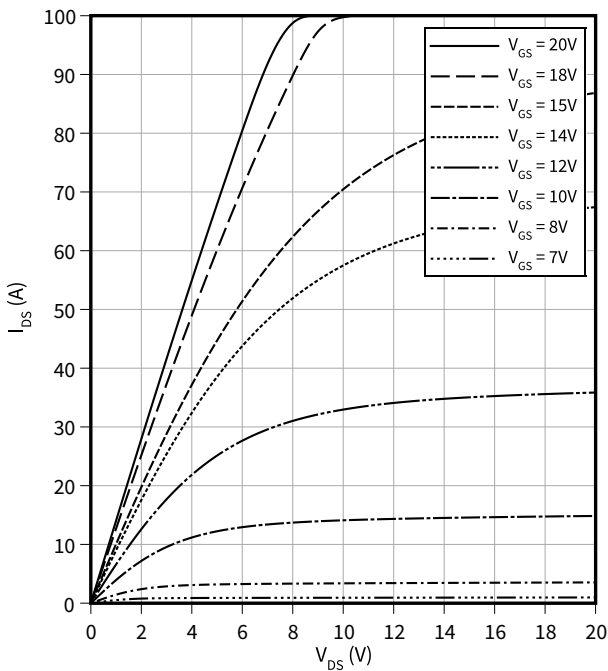
**Typical gate-source threshold voltage as a function of junction temperature**

$V_{GS(th)} = f(T_{vj})$   
 $I_D = 2.8\text{ mA}$



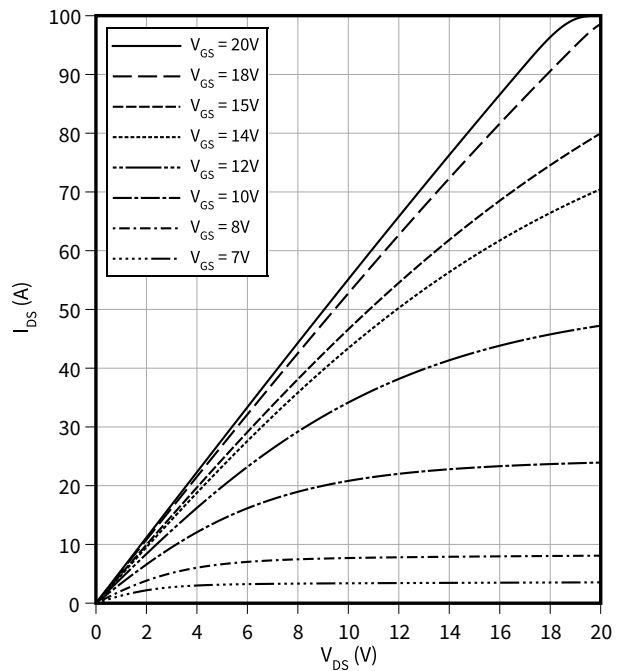
**Typical output characteristic,  $V_{GS}$  as parameter**

$I_{DS} = f(V_{DS})$   
 $T_{vj} = 25\text{ °C}$ ,  $t_p = 20\ \mu\text{s}$



**Typical output characteristic,  $V_{GS}$  as parameter**

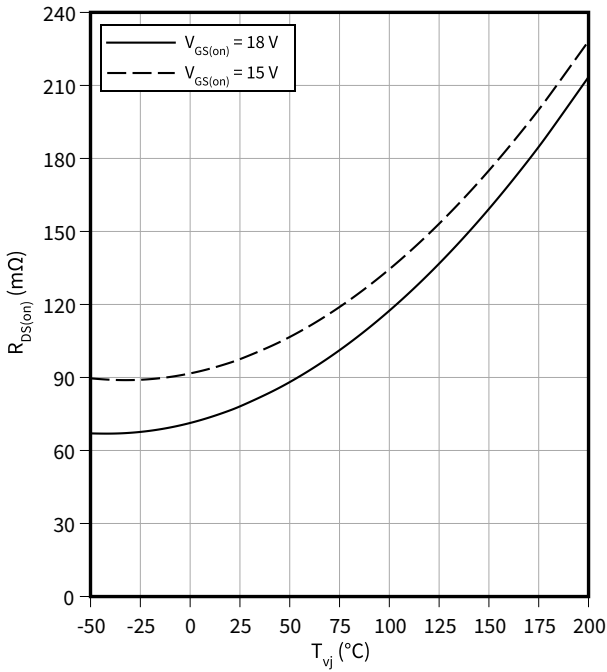
$I_{DS} = f(V_{DS})$   
 $T_{vj} = 175\text{ °C}$ ,  $t_p = 20\ \mu\text{s}$



4 Characteristics diagrams

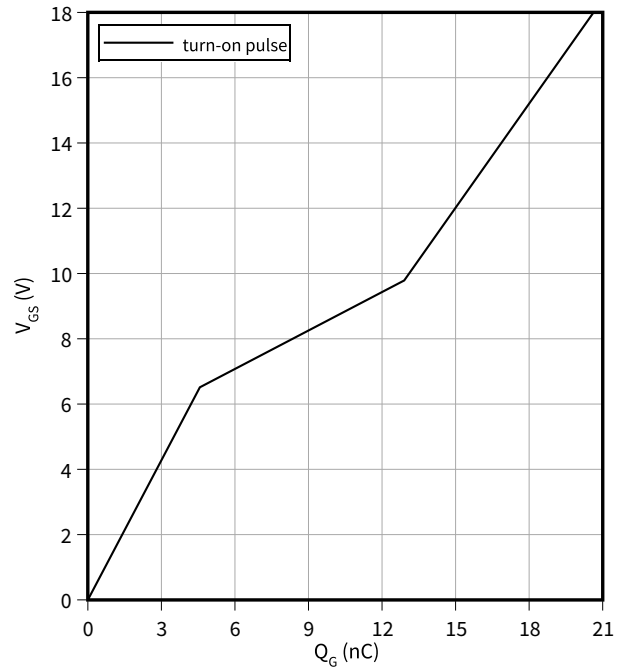
**Typical on-state resistance as a function of junction temperature**

$R_{DS(on)} = f(T_{vj})$   
 $I_D = 8.9 \text{ A}$



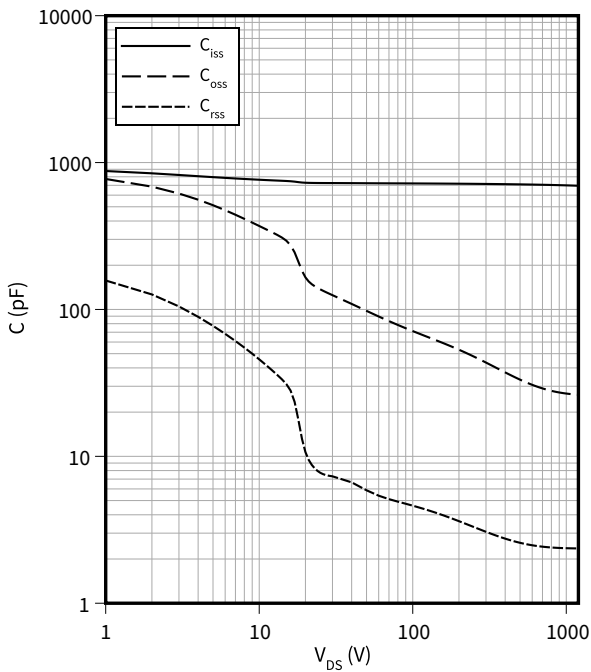
**Typical gate charge**

$V_{GS} = f(Q_G)$   
 $I_D = 8.9 \text{ A}, V_{DS} = 800 \text{ V}$



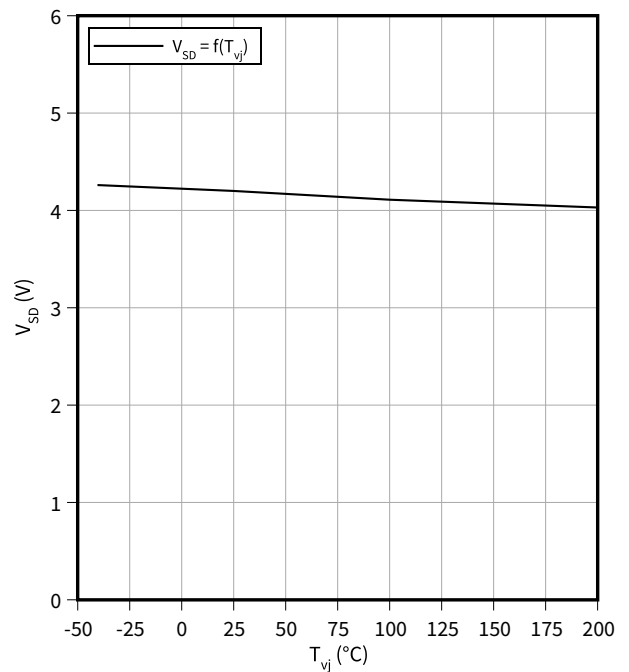
**Typical capacitance as a function of drain-source voltage**

$C = f(V_{DS})$   
 $f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$



**Typical reverse drain voltage as function of junction temperature**

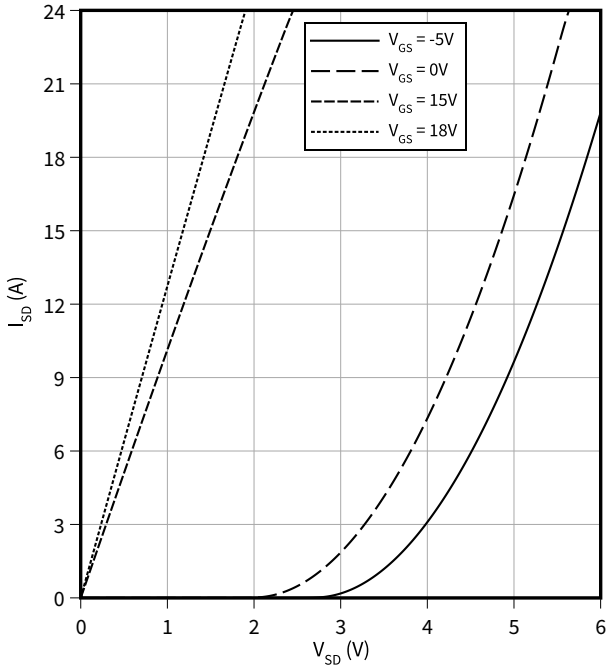
$V_{SD} = f(T_{vj})$   
 $I_{SD} = 8.9 \text{ A}, V_{GS} = 0 \text{ V}$



4 Characteristics diagrams

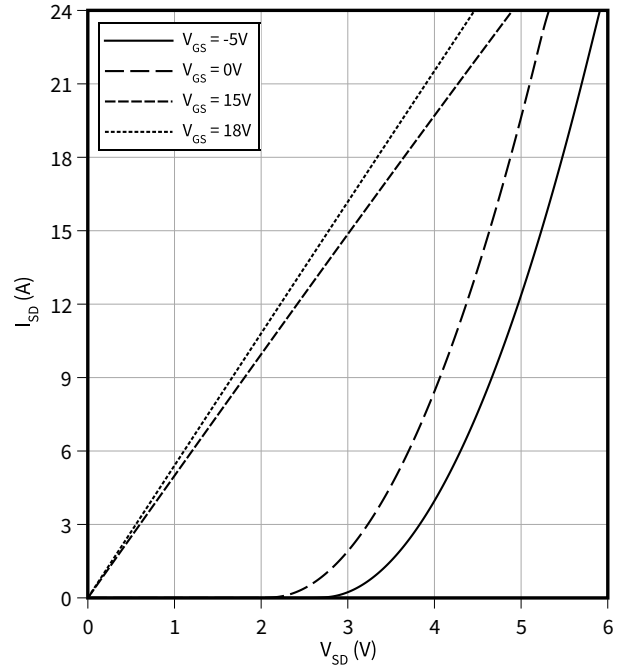
**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$   
 $T_{vj} = 25\text{ °C}$ ,  $t_p = 20\text{ }\mu\text{s}$



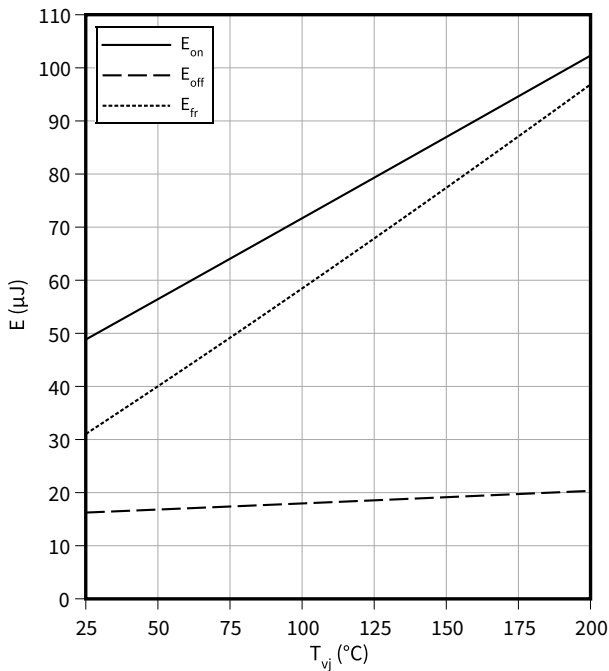
**Typical reverse drain current as function of reverse drain voltage,  $V_{GS}$  as parameter**

$I_{SD} = f(V_{SD})$   
 $T_{vj} = 175\text{ °C}$ ,  $t_p = 20\text{ }\mu\text{s}$



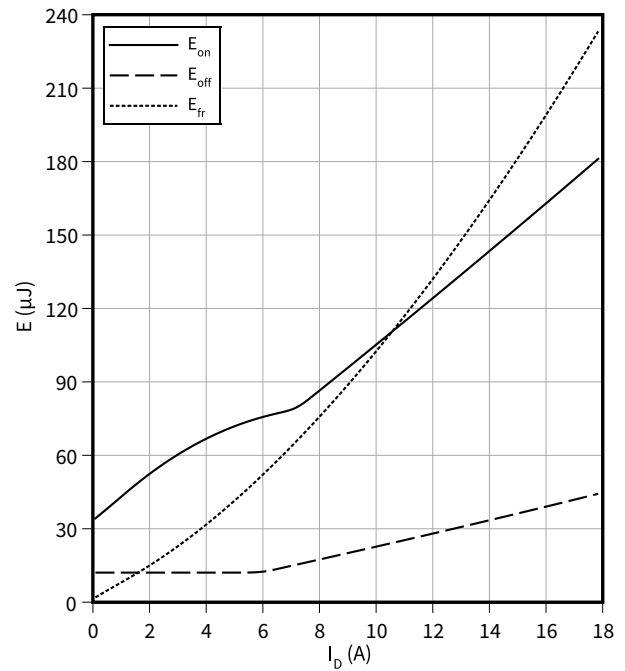
**Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(T_{vj})$   
 $V_{GS} = 0/18\text{ V}$ ,  $I_D = 8.9\text{ A}$ ,  $R_{G,ext} = 2.3\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$



**Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(I_D)$   
 $V_{GS} = 0/18\text{ V}$ ,  $T_{vj} = 175\text{ °C}$ ,  $R_{G,ext} = 2.3\text{ }\Omega$ ,  $V_{DD} = 800\text{ V}$

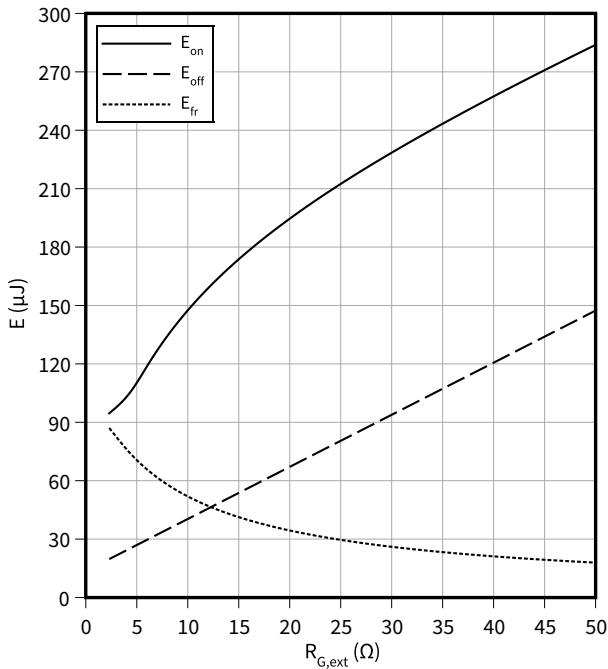


4 Characteristics diagrams

**Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$E = f(R_{G,ext})$

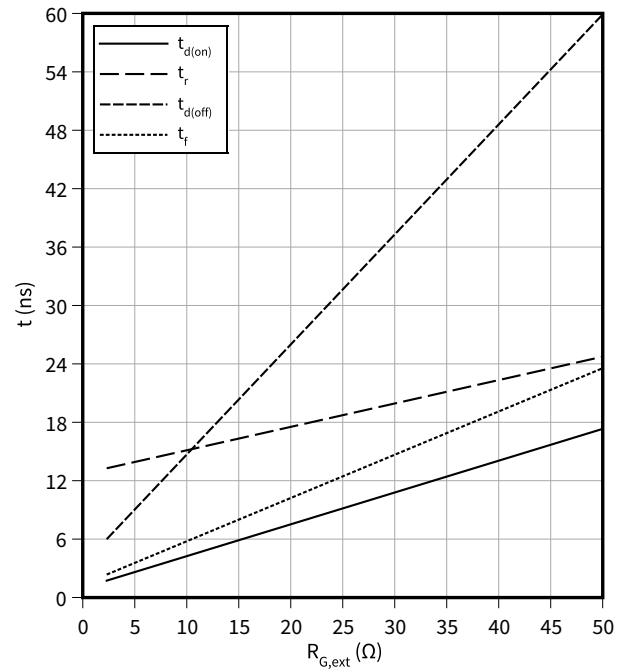
$V_{GS} = 0/18\text{ V}$ ,  $I_D = 8.9\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



**Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$t = f(R_{G,ext})$

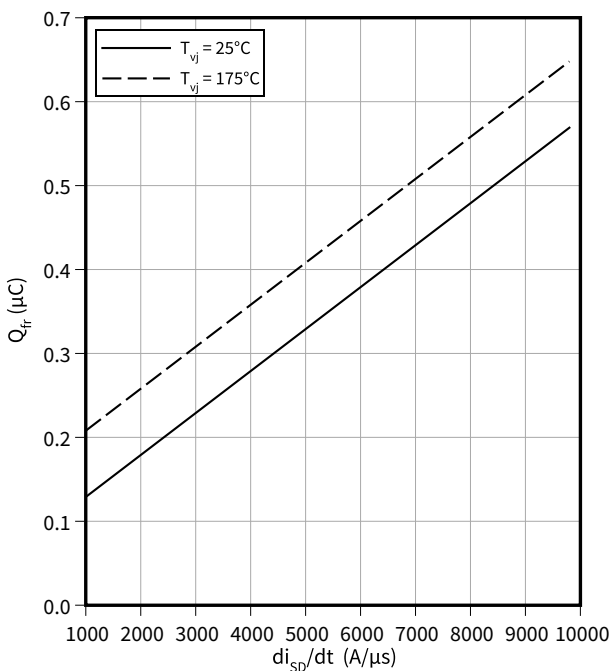
$V_{GS} = 0/18\text{ V}$ ,  $I_D = 8.9\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $V_{DD} = 800\text{ V}$



**Typical reverse recovery charge as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$Q_{fr} = f(di_{SD}/dt)$

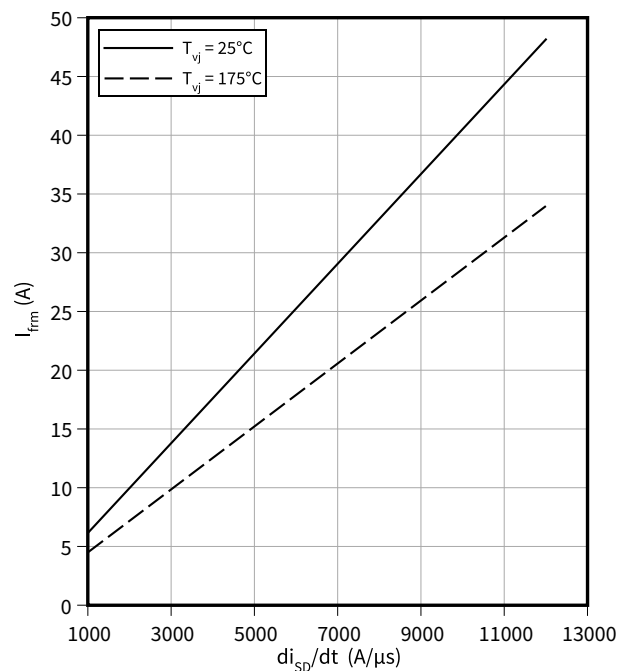
$V_{GS} = 0/18\text{ V}$ ,  $I_{SD} = 8.9\text{ A}$ ,  $V_{DD} = 800\text{ V}$



**Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = 0\text{ V}$**

$I_{frm} = f(di_{SD}/dt)$

$V_{GS} = 0/18\text{ V}$ ,  $I_{SD} = 8.9\text{ A}$ ,  $V_{DD} = 800\text{ V}$



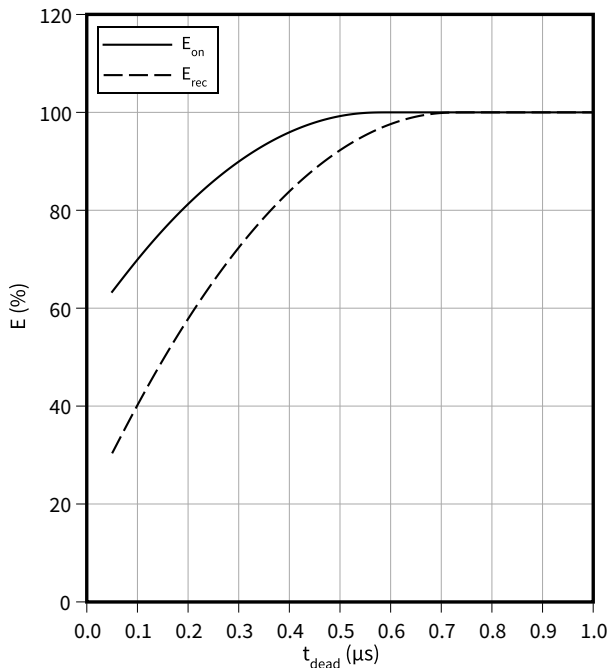
4 Characteristics diagrams

**Typical switching energy as a function of dead time / blanking time, test circuit in Fig. F, 2nd device own body diode:  $V_{GS} = -5\text{ V}$**

$$E = f(t_{\text{dead}})$$

$V_{GS} = 0/18\text{ V}$ ,  $I_D = 8.9\text{ A}$ ,  $T_{vj} = 175\text{ °C}$ ,  $R_{G,\text{ext}} = 2.3\ \Omega$

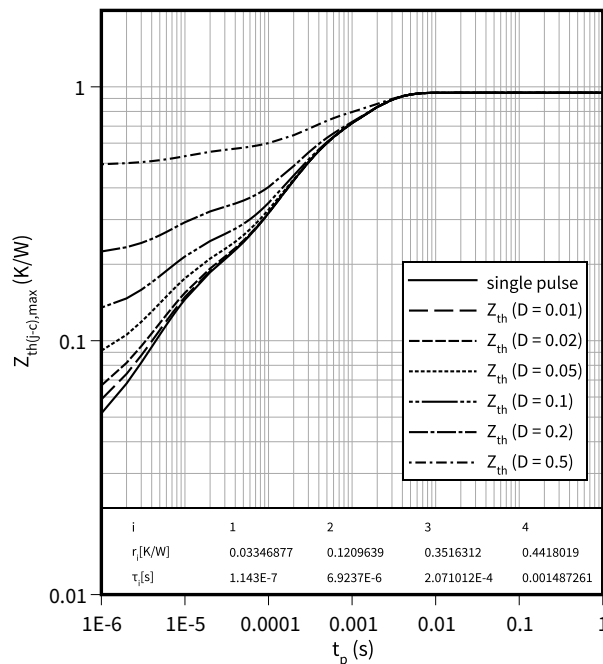
$V_{DD} = 800\text{ V}$



**Max. transient thermal impedance (MOSFET/diode)**

$$Z_{\text{th}(j-c),\text{max}} = f(t_p)$$

$$D = t_p/T$$



5 Package outlines

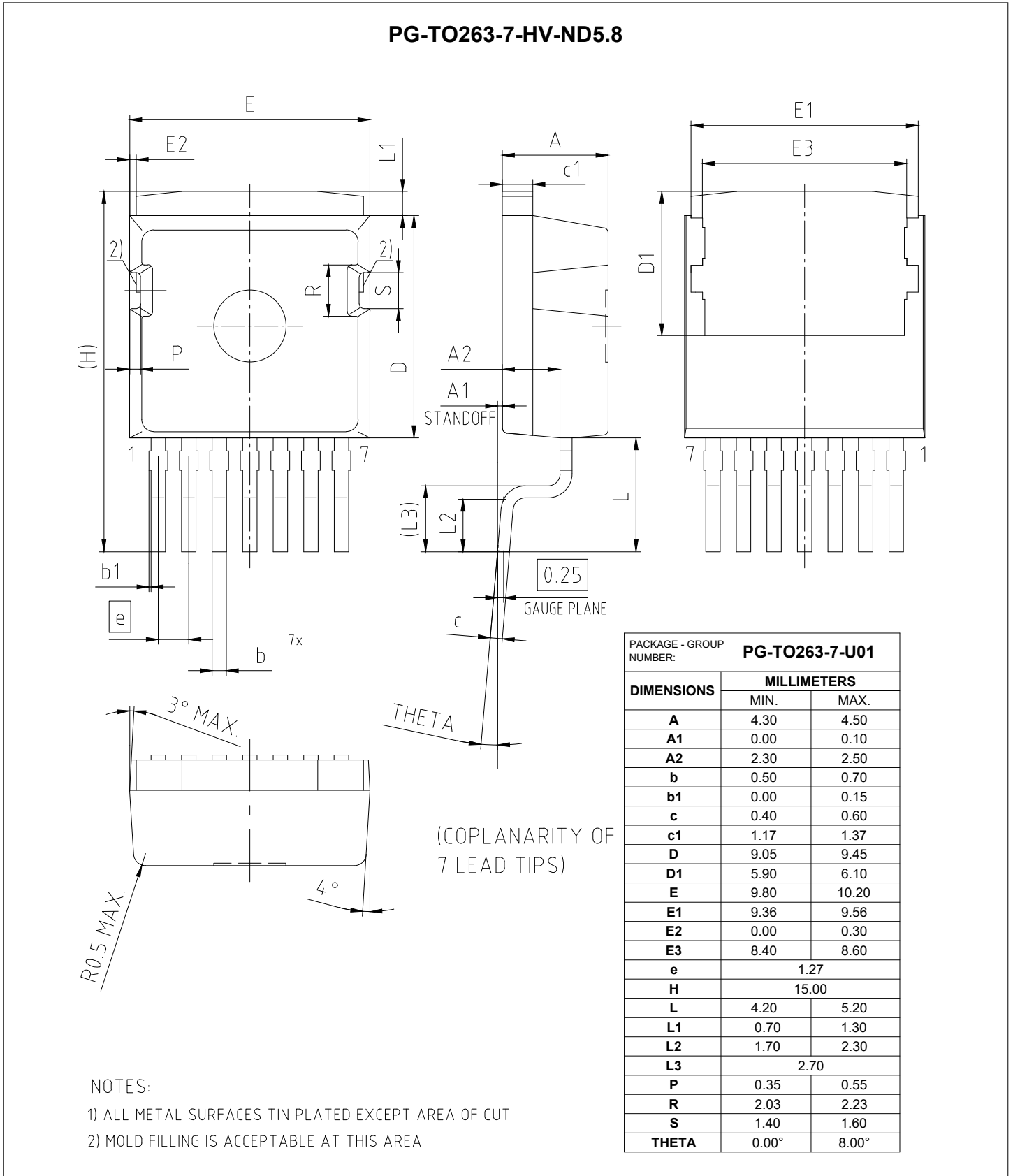


Figure 1

## 6 Testing conditions

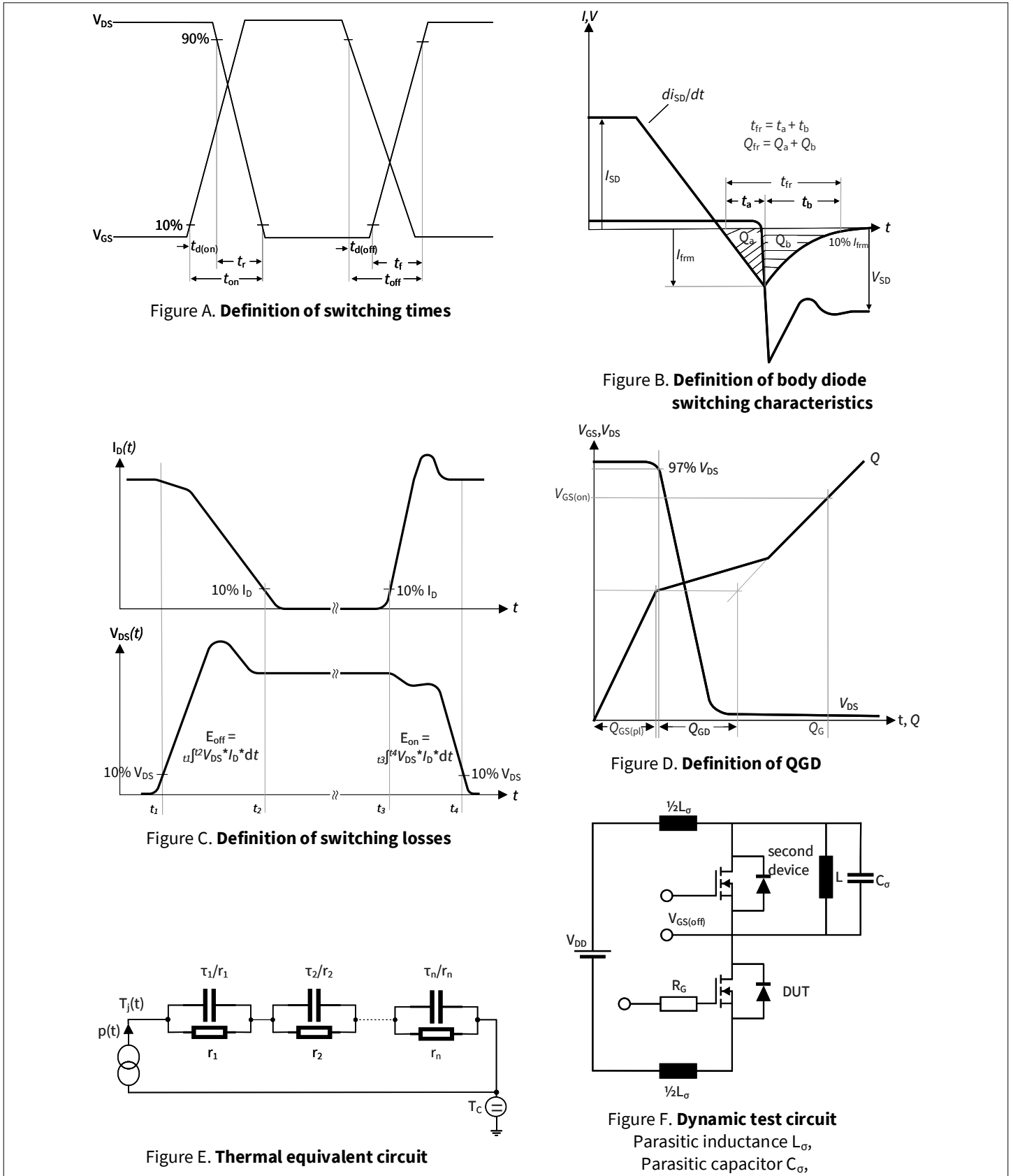


Figure 2

## Revision history

Document revision	Date of release	Description of changes
0.10	2023-08-09	Preliminary datasheet
1.00	2023-10-05	Final datasheet
1.10	2024-01-11	Negative gate voltage values updated Resistance parameters updated Additional capacitance & charge values added E = f(t <sub>dead</sub> ) graph y-axis correction to percentage values Editorial changes



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